

Material Composition Declaration

Package Information

Package	Package Weight (mg)	Terminal Finish	MSL Rating
SOD-323	4	Matte Tin (Sn)	1

Product Group

Type No.	Description
SD101AWS – SD101CWS	Diode Schottky 15mA 40V – 60V
RB751V-40	Diode Schottky 30mA 30V
BAS70WS	Diode Schottky 70mA 70V
1SS357	Diode Schottky 100mA 40V
RB501V-40	Diode Schottky 100mA 40V
MMDL101	Diode Schottky 200mA 7V
MMDL717WS	Diode Schottky 200mA 20V
BAT42WS / BAT43WS	Diode Schottky 200mA 30V
BAT54HS / BAT54WS	Diode Schottky 200mA 30V
MMDL301	Diode Schottky 200mA 30V
BAS40WS	Diode Schottky 200mA 40V
MMDL770	Diode Schottky 200mA 70V
1SS404	Diode Schottky 300mA 20V
SD103AWS – SD103CWS	Diode Schottky 350mA 20V – 40V
RB551V-30	Diode Schottky 500mA 20V
SS0520WS – SS0540WS	Diode Schottky 500mA 20V – 40V
SS1020WS – SS1040WS	Diode Schottky 1000mA 20V – 40V
BAT60B	Diode Schottky 3000mA 10V
1SS380	Diode Switching 100mA 35V
1SS355	Diode Switching 100mA 80V
1N4148WS	Diode Switching 150mA 75V
BAV16WS	Diode Switching 150mA 75V
MMDL6050	Diode Switching 200mA 70V
BAS16H	Diode Switching 200mA 100V
MMDL914	Diode Switching 200mA 100V
BAV19WS – BAV21WS	Diode Switching 200mA 120V – 250V
BAS20H	Diode Switching 200mA 200V
BAS21H	Diode Switching 200mA 250V
1N4448WS	Diode Switching 250mA 75V
BAS316	Diode Switching 250mA 100V
BZT52B2V4S – BZT52B75S	Diode Zener 200mW
BZT52C2V0S – BZT52C51S	Diode Zener 200mW
MMSZ5221BS – MMSZ5262BS	Diode Zener 200mW

Component	Material	Substance	CAS No.	Material Mass (%)	Material Mass (mg)	Component Mass (%)	Component Mass (mg)	PPM
Die	Doped Silicon*	Si	7440-21-3	100.00	0.049	1.23	0.049	12250
Wire Bond	Gold	Au	7440-57-5	100.00	0.004	0.11	0.004	1000
Leadframe	Ferrous Alloy	Fe	7439-89-6	56.40	0.549	24.33	0.973	137193
		Ni	7440-02-0	42.00	0.409			102165
		Mn	7439-96-5	0.80	0.008			1946
		Co	7440-48-4	0.50	0.005			1216.25
		Si	7440-21-3	0.30	0.003			729.75
Die Bond	Silver Silicone	Ag	7440-22-4	80.00	0.030	0.95	0.038	7600
		Bisphenol F	28064-14-4	15.00	0.006			1425
		Glycidyl neodeconate	26761-45-5	5.00	0.002			475
Plating	Matte Tin	Sn	7440-31-5	100.00	0.115	2.88	0.115	28750
Encapsulation	EMC	Silica	7631-86-9	79.00	2.229	70.50	2.821	557147.5
		Epoxy Resin	29690-82-2	20.00	0.564			141050
		Carbon Black	1333-86-4	1.00	0.028			7052.5

Tolerance ±10%

*Dopant and metallization of the silicon die are not reported in this statement where their concentration is less than the minimum reportable level per EIA JIG-101.

Data disclosed herewith is approximate and is based on information from suppliers surveys, Material Safety Datasheet, engineering calculations and measurements. Won-Top Electronics(WTE) has checked all information carefully and believes it to be correct and accurate. However, WTE cannot assume any responsibility for inaccuracies. WTE reserves the right to change any or all information herein without further notice.

RoHS Declaration

The European Parliament and of the Council on the Restriction of the use of Certain Hazardous Substances in Electrical and Electronics Equipment (RoHS) directive restricts the concentration of Lead (Pb), Mercury (Hg), Hexavalent Chromium (Cr6+), Polybrominated Biphenyls (PBB), Polybrominated Diphenyl Ethers (PBD) to 0.1%(1000 PPM) and restricts the concentration of Cadmium (Cd) to 0.01%(100 PPM) in homogeneous materials of electronics products.

The product group listed above and the homogenous materials are compliant with the Directive 2011/65/EU. WTE warrants that all its packing, components and/or products supplied to the Customer and/or its affiliated companies or designated contractors do not contain these hazardous substances in quantity levels higher than or equal to the thresholds to this directive.

Exemptions as declared for the directive are:

- 7(a) Lead in high melting temperature type solders (i.e. lead-based alloys containing 85% by weight or more lead).
- 7(c)-I Lead in glass (applicable for glass passivated silicon die).